

The EL-325 is a GaAs IRED mounted in a low profile clear epoxy package. This IRED is both compact and easy to mount.

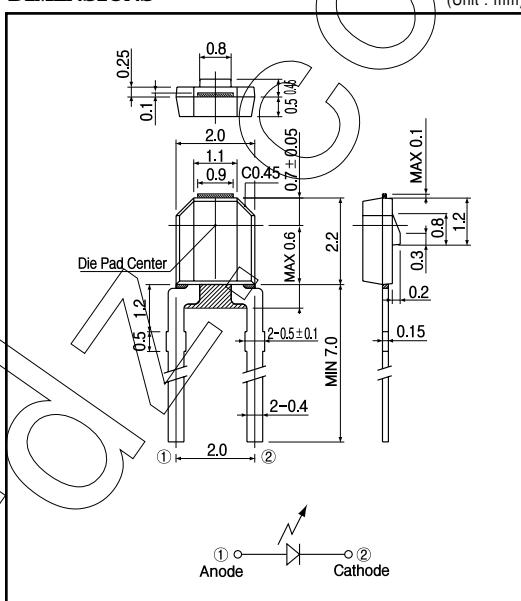
FEATURES

- Ultra compact
- Low profile
- Snap-in mount is possible

APPLICATIONS

- Photointerrupters
- Optical equipment

DIMENSIONS



MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Reverse voltage	V_R	5	V
Forward current	I_F	50	mA
Power dissipation	P_D	100	mW
Pulse forward current ^{*1}	I_{FP}	0.5	A
Operating temp.	Topr.	-25 +85	
Storage temp.	Tstg.	-30 +85	
Soldering temp. ^{*2}	Tsol.	260	

*1. pulse width : tw 100 μ sec. period : T=10msec.

*2. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

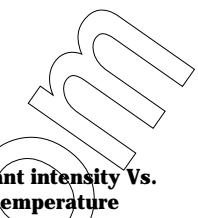
(Ta=25)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V_F	$I_F=50\text{mA}$			1.6	V
Reverse current	I_R	$V_R=5\text{V}$			10	μA
Peak emission wavelength	λ	$I_F=50\text{mA}$	940			nm
Spectral bandwidth		$I_F=50\text{mA}$		50		nm
Radiant intensity ^{*3}	P_O	$I_F=50\text{mA}$		0.7		mW/sr
Half angle				± 50		deg.

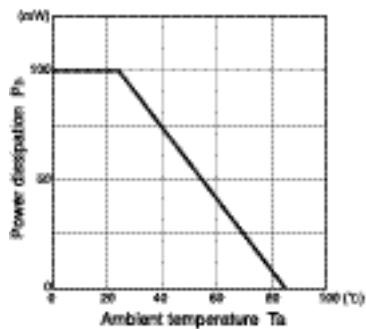
*3. Measured by tester of KODENSHI CORP.

Infrared Emitting Diodes(GaAs)

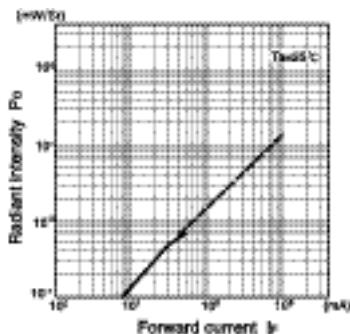
EL - 325



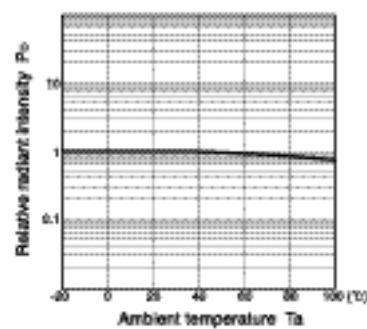
**Power dissipation Vs.
Ambient temperature**



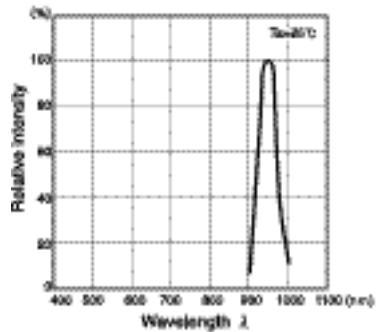
**Radiant intensity Vs.
Forward current**



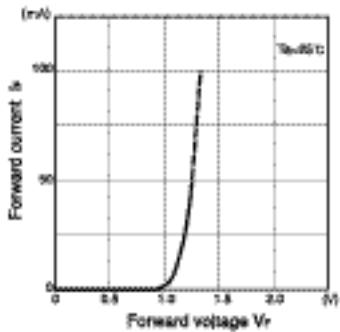
**Relative radiant intensity Vs.
Ambient temperature**



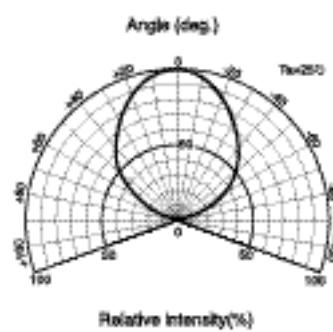
**Relative intensity Vs.
Wavelength**



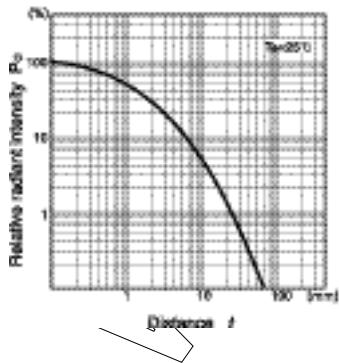
**Forward current vs.
Forward voltage**



Radiant Pattern



**Relative radiant intensity Vs.
Distance**



Relative radiant intensity Vs.
Distance test method

